IN THE CLAIMS:

Please amend the claims as follows:

1. (Currently Amended) A method for fabricating a mask on a substrate comprising:
forming a ~~substrate including: a~~ first layer of attenuating material over a portion of the substrate;
forming a second layer of attenuating material over a portion of the first layer of attenuating material; ~~and~~
forming an opaque layer over a portion of the second layer of attenuating material;
etching the substrate to form at least one completely transmissive region;
etching the substrate to form at least one slightly attenuated region, the etching including forming a patterned resist over the substrate; and
etching the substrate to form at least one highly attenuated region.

2. (Previously presented) The method according to claim 1, wherein etching the substrate to form the at least one completely transmissive region comprises forming a first patterned resist over the opaque layer of the substrate and etching the substrate to form a plurality of isolated completely transmissive regions and a plurality of closely spaced completely transmissive regions.

3. (Previously presented) The method according to claim 2, wherein etching the substrate to form the at least one slightly attenuated region comprises removing portions of the opaque layer and the second layer of attenuating material to form a plurality of slightly attenuated regions, each of the plurality of slightly attenuated regions being positioned at an edge defining one of the plurality of isolated completely transmissive regions.

4. (Canceled)

5. (Previously presented) The method according to claim 2, wherein etching the substrate to form the at least one highly attenuated region comprises removing portions of the

opaque layer to form a plurality of highly attenuated regions, each of the plurality of highly attenuated regions being positioned at an edge defining one of the plurality of closely spaced completely transmissive regions.

6. (Previously presented) The method according to claim 5, wherein etching the substrate to form the plurality of highly attenuated regions comprises forming a third patterned resist over the substrate.

7. (Previously presented) The method according to claim 1, wherein forming the substrate further comprises forming the substrate to include an etch stop layer between the first layer of attenuating material and the second layer of attenuating material.

8. (Previously presented) The method according to claim 7, wherein etching the substrate to form the at least one completely transmissive region comprises forming a first patterned resist over the opaque layer of the substrate and etching the substrate to form a plurality of isolated completely transmissive regions and a plurality of closely spaced completely transmissive regions.

9. (Previously presented) The method according to claim 8, wherein etching the substrate to form the at least one slightly attenuated region comprises removing portions of the opaque layer and the second layer of attenuating material in a single etch step to form a plurality of slightly attenuated regions, each of the plurality of slightly attenuated regions being positioned at an edge defining one of the plurality of isolated completely transmissive regions.

10. (Previously presented) The method according to claim 9, wherein etching the substrate to form the at least one highly attenuated region comprises removing portions of the opaque layer to form a plurality of highly attenuated regions, each of the plurality of highly attenuated regions being positioned at an edge defining one of the plurality of closely spaced completely transmissive regions.

11. (Previously presented) The method according to claim 10, wherein etching the substrate to form the plurality of highly attenuated regions comprises forming a third patterned resist over the substrate.

12. (Currently Amended) A attenuated phase shift mask for a substrate comprising:

~~a transparent substrate;~~

forming a plurality of isolated completely transmissive regions and a plurality of other regions on the substrate;

forming a plurality of slightly attenuated regions, each of the plurality of slightly attenuated regions being formed at an edge defining one of the plurality of isolated completely transmissive regions on the substrate;

forming a plurality of completely transmissive regions on the substrate; ~~and~~

forming a plurality of highly attenuated regions, each of the plurality of highly attenuated regions being formed at an edge defining one of the plurality of isolated completely transmissive regions, the plurality of highly attenuated regions comprising a first layer of attenuating material, a layer of etch stop material, and a second layer of attenuating material on the substrate.

13. (Previously presented) The phase shift mask of claim 12, further comprising a plurality of opaque regions.

14. (Previously presented) The phase shift mask of claim 13, wherein the plurality of opaque regions comprise chromium.

15. (Previously presented) The phase shift mask of claim 12, wherein the transparent substrate comprises a material selected from a group consisting of quartz, fused silica, and glass.

16. (Previously presented) The phase shift mask of claim 12, wherein the plurality of slightly attenuated regions comprises a layer of attenuating material selected from a group consisting of chromium oxynitride and chromium fluoride.

17. (Canceled)

18. (Previously presented) The phase shift mask of claim 12, wherein the first layer of attenuating material is selected from a group consisting of chromium oxynitride and chromium fluoride and the second layer of attenuating material comprises molybdenum silicide oxynitride.

19. (Previously presented) The phase shift mask of claim 12, wherein the plurality of slightly attenuated regions comprises a layer of attenuating material and a layer of etch stop material.

20. (Previously presented) The phase shift mask of claim 19, wherein the layer of attenuating material is selected from a group consisting of chromium oxynitride and chromium fluoride and the layer of etch stop material comprises silicon dioxide.

21. (Previously presented) The phase shift mask of claim 12, wherein the first layer of attenuating material is selected from a group consisting of chromium oxynitride and chromium fluoride, the layer of etch stop material comprises silicon dioxide, and the second layer of attenuating material comprises molybdenum silicide oxynitride.